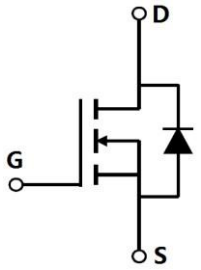
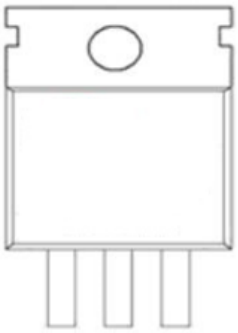
100V N-SGT Enhancement Mode MOSFET

General Description

130N10 use advanced SGT MOSFET technology to provide low RDS(ON), low gate charge, fast switching and excellent avalanche characteristics.

This device is specially designed to get better ruggedness and suitable to use in





Features

Low RDS(on) & FOM

Extremely low switching loss

Excellent stability and uniformity or Invertors

Applications

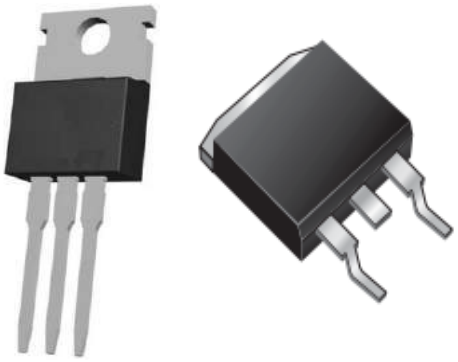
Consumer electronic power supply

Motor control

Synchronous-rectification

Isolated DC

Synchronous-rectification applications



Absolute Maximum Ratings at T_j=25℃ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	VDS	100	V
Gate source voltage	VGS	±20	V
Continuous drain current[1], T_C=25 ℃	ID	130	A
Pulsed drain current[2], T_C=25 ℃	ID, pulse	390	A
Power dissipation3 TC=25 ℃	P_D	192	W
Single pulsed avalanche energy[5]	EAS	400	mJ
Operation and storage temperature	Tstg，Tj	-55 to 150	℃
Thermal resistance, junction-case	RθJC	0.65	℃/W
Thermal resistance, junction-ambient[4]	RθJA	62	℃/W

Electrical Characteristics at T_j=25 ℃ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	100			V	V_{GS}=0 V, I_D=250 μA
Gate threshold voltage	$V_{GS(th)}$	2.0		4.0	V	V_{DS}=V_{GS}, I_D=250 μA
Drain-source on-state resistance	$R_{DS(ON)}$		4.0	4.6	mΩ	V_{GS}=10 V, I_D=60 A
Gate-source leakage current	I_{GSS}			100	nA	V_{GS}=20 V
				-100		V_{GS}=-20 V
Drain-source leakage current	I_{DSS}			1	μA	V_{DS}=100 V, V_{GS}=0 V
Input capacitance	C_{iss}		6124.6		pF	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz
Output capacitance	C_{oss}		792.3		pF	
Reverse transfer capacitance	C_{rss}		15.1		pF	
Turn-on delay time	$t_{d(on)}$		28.2		ns	V_{GS}=10 V, V_{DS}=50 V, R_G=2.2 Ω, I_D=22 A
Rise time	t_r		7.5		ns	
Turn-off delay time	$t_{d(off)}$		81.9		ns	
Fall time	t_f		20.1		ns	
Total gate charge	Q_g		101.6		nC	I_D=22 A, V_{DS}=50 V, V_{GS}=10 V
Gate-source charge	Q_{gs}		20.6		nC	
Gate-drain charge	Q_{gd}		28.7		nC	
Gate plateau voltage	$V_{plateau}$		4.2		V	
Diode forward current	I_S			130	A	V_{GS}<V_{th}
Pulsed source current	I_{SP}			390		
Diode forward voltage	V_{SD}			1.3	V	I_S=20 A, V_{GS}=0 V
Reverse recovery time	t_{rr}		82.1		ns	I_S=10 A, di/dt=100 A/μs
Reverse recovery charge	Q_{rr}		248.4		nC	
Peak reverse recovery current	I_{rrm}		4.9		A	

Note

1、Calculated continuous current based on maximum allowable junction temperature.

2、Repetitive rating; pulse width limited by max. junction temperature.

3、Pd is based on max. junction temperature, using junction-case thermal resistance.

4、The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_a=25 ℃.

5、V_{DD}=50 V, R_G=25 Ω, L=0.5 mH, starting T_j=25 ℃.

Electrical Characteristics Diagrams

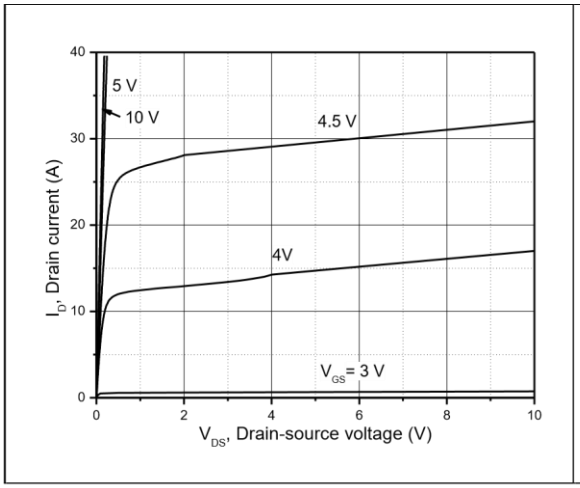


Figure 1, Typ. output characteristics

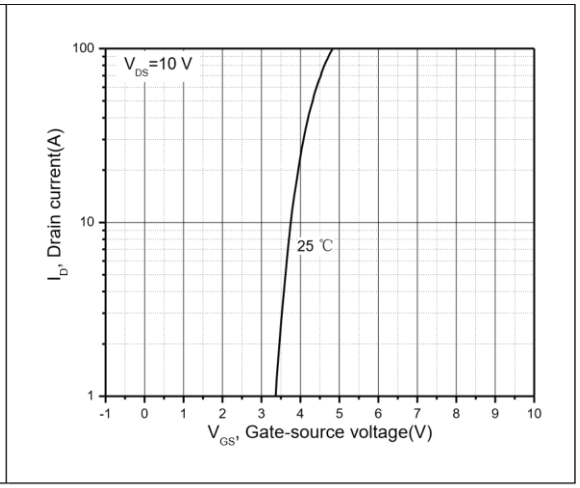


Figure 2, Typ. transfer characteristics

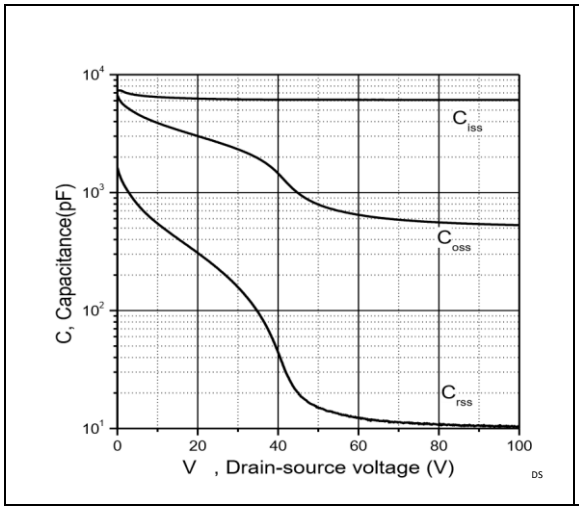


Figure 3, Typ. capacitances

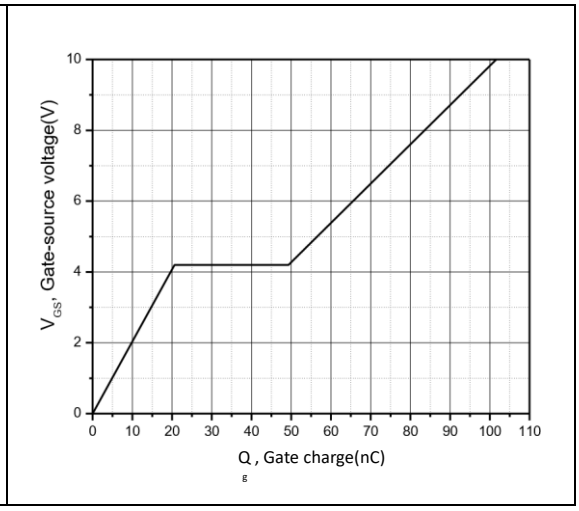


Figure 4, Typ. gate charge

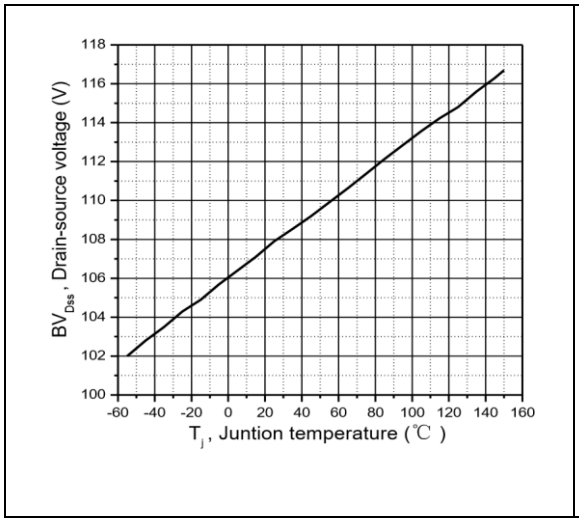


Figure 5, Drain-source breakdown voltage

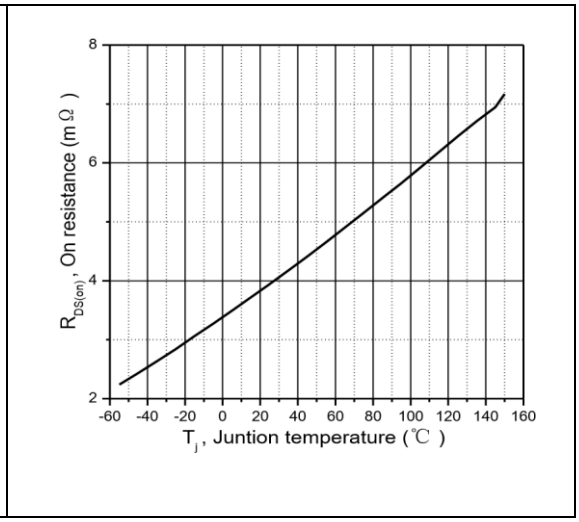


Figure 6, Drain-source on-state resistance

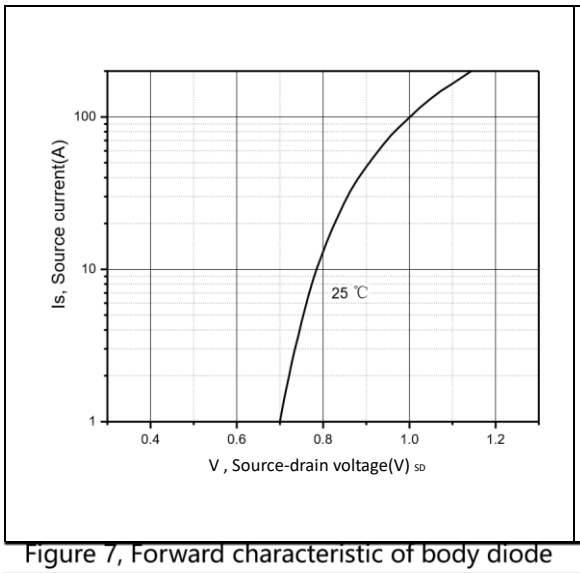


Figure 7, Forward characteristic of body diode

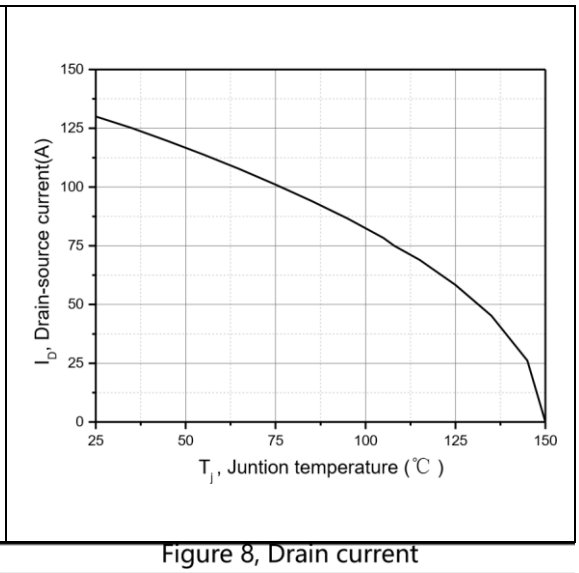


Figure 8, Drain current

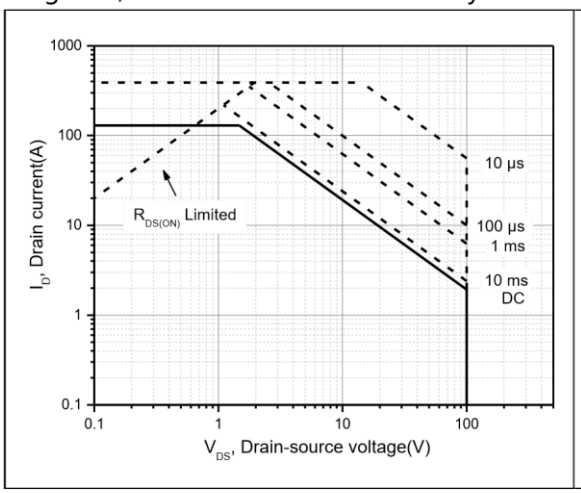


Figure 9, Safe operation area for TO220/TO263

T_C=25 ℃

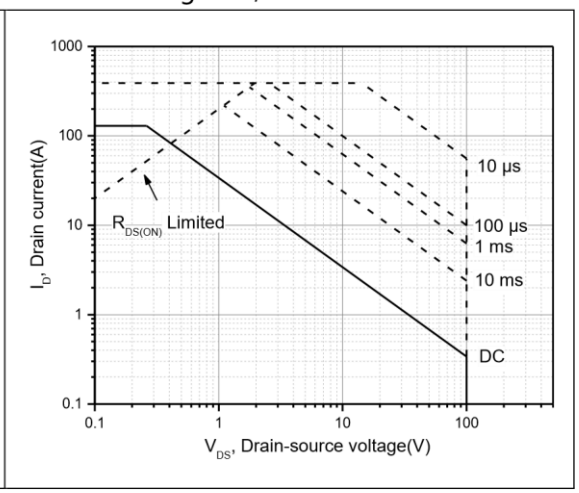


Figure 10, Safe operation area for TO220F

T_C=25 ℃

■ Test circuits and waveforms

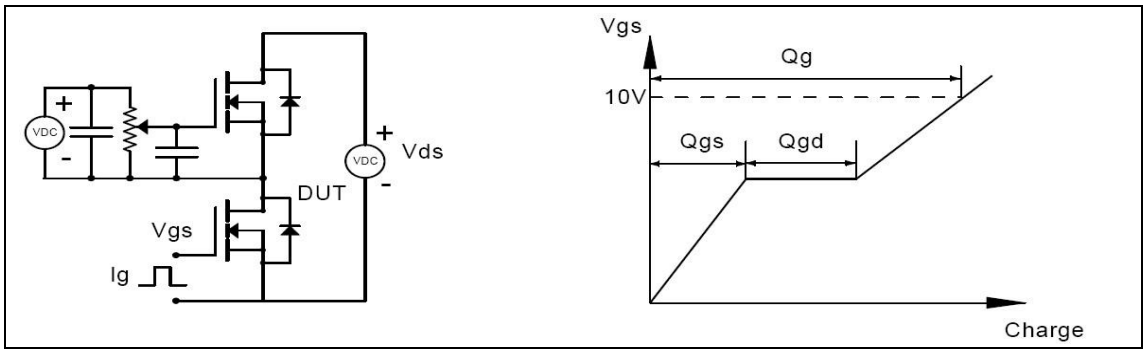


Figure 1, Gate charge test circuit & waveform

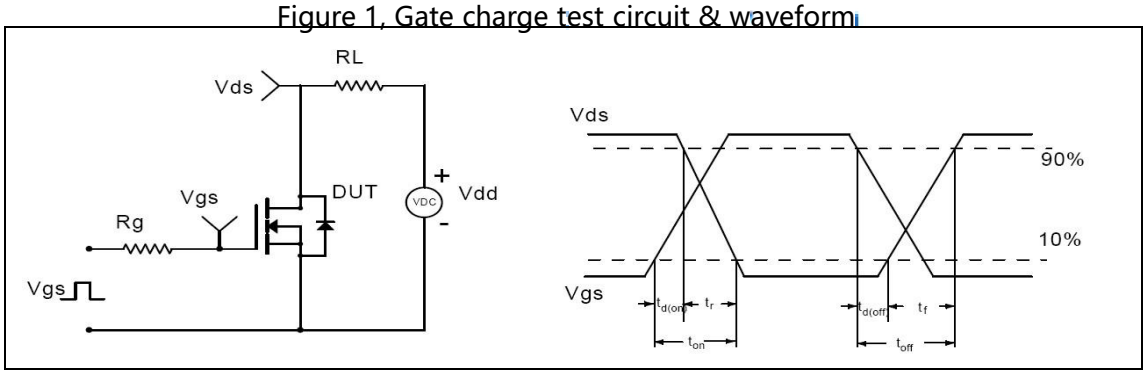


Figure 2, Switching time test circuit & waveforms

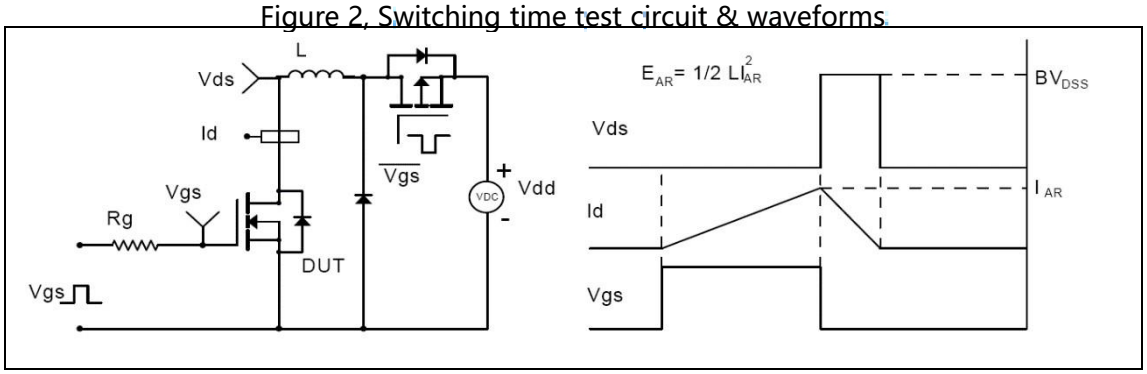


Figure 3, Unclamped inductive switching (UIS) test circuit & waveforms

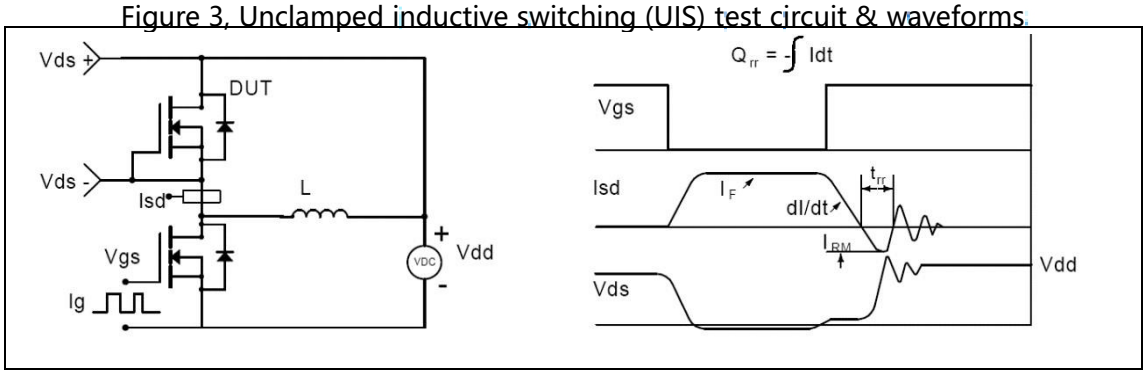
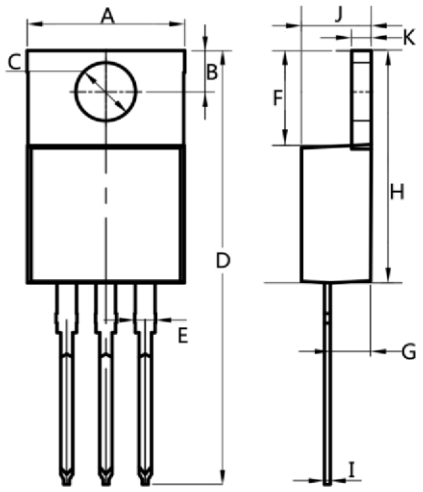


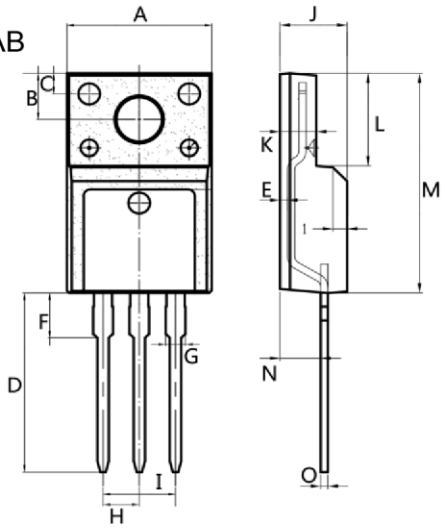
Figure 4, Diode reverse recovery test circuit & waveforms

TO-220AB



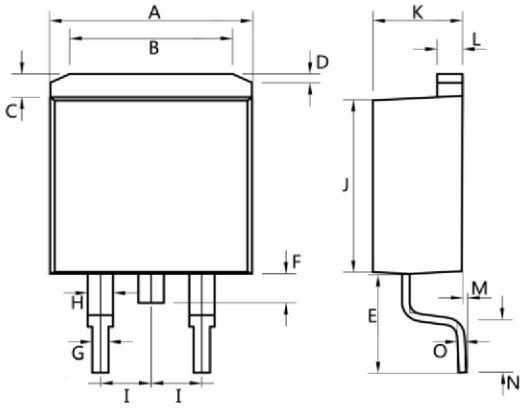
Dim.	Min.	Max.
A	10.0	10.4
B	2.5	3.0
C	3.5	4.0
D	28.0	30.0
E	1.1	1.5
F	6.2	6.6
G	2.9	3.3
H	15.0	16.0
I	0.35	0.45
J	4.3	4.7
K	1.2	1.4
All Dimensions in millimeter		

ITO-220AB



Dim.	Min.	Max.
A	9.9	10.3
B	2.9	3.5
C	1.15	1.45
D	12.75	13.25
E	0.55	0.75
F	3.1	3.5
G	1.25	1.45
H	Typ 2.54	
I	Typ 5.08	
J	4.55	4.75
K	2.4	2. 7
L	6.35	6.75
M	15.0	16.0
N	2.75	3.15
O	0.45	0.60
All Dimensions in millimeter		

TO-263



Dim.	Min.	Max.
A	10.0	10. 5
B	7.25	7.75
C	1.3	1.5
D	0.55	0.75
E	5.0	6.0
F	1.4	1.6
G	0.75	0.95
H	1.15	1.35
I	Typ 2.54	
J	8.4	8.6
K	4.4	4.6
L	1.25	1.45
M	0.02	0.1
N	2.4	2.8
O	0.35	0.45
All Dimensions in millimeter		